

7. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;

irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

D² treating a surface of the semiconductor film with a hydrofluoric acid to remove a natural oxidation film formed on the surface of the semiconductor film after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating after the treatment with said hydrofluoric acid.